

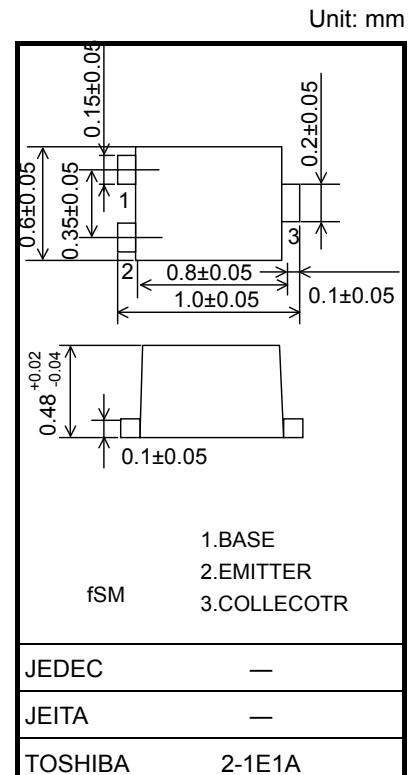
TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT3S14FS

VHF~UHF Band Low-Noise Amplifier Applications

VHF~UHF Band Buffer Applications

- Superior performance in buffer applications
- Superior noise characteristics
:NF = 1.7 dB, $|S_{21e}|^2 = 7$ dB (f = 2GHz)



Absolute Maximum Ratings (Ta = 25°C)

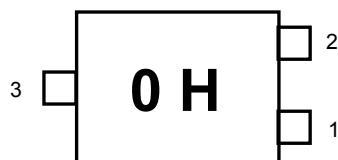
| Characteristic | Symbol | Rating | Unit |
|-----------------------------|-----------------------|---------|------|
| Collector- base voltage | V _{CBO} | 6 | V |
| Collector- emitter voltage | V _{CEO} | 2.5 | V |
| Emitter- base voltage | V _{EBO} | 1.5 | V |
| Collector current | I _C | 30 | mA |
| Base current | I _B | 10 | mW |
| Collector power dissipation | P _C (Note) | 85 | mW |
| Junction temperature | T _j | 125 | °C |
| Storage temperature range | T _{stg} | -55~125 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note: 10 mm² × 1.0 mm (t), mounted on a glass-epoxy printed circuit board.

Marking



Microwave Characteristics (Ta = 25°C)

| Characteristic | Symbol | Condition | Min | Typ. | Max | Unit |
|----------------------|-------------------------------------|--|-----|------|-----|------|
| Transition frequency | f _T | V _{CE} = 1 V, I _C = 5 mA | 9 | 11 | — | GHz |
| Insertion gain | S _{21e} ² (1) | V _{CE} = 1 V, I _C = 5 mA, f = 2 GHz | — | 7 | — | dB |
| | S _{21e} ² (2) | V _{CE} = 2 V, I _C = 15 mA, f = 2 GHz | 6.5 | 9 | — | |
| Noise figure | NF | V _{CE} = 1 V, I _C = 5 mA, f = 2 GHz | — | 1.7 | 3 | dB |

Electrical Characteristics (Ta = 25°C)

| Characteristic | Symbol | Condition | Min | Typ. | Max | Unit |
|------------------------------|------------------|---|-----|------|------|------|
| Collector cutoff current | I _{CB0} | V _{CB} = 4 V, I _E = 0 | — | — | 0.1 | μA |
| Emitter cutoff current | I _{EB0} | V _{EB} = 1 V, I _C = 0 | — | — | 1 | μA |
| DC current gain | h _{FE} | V _{CE} = 1 V, I _C = 5 mA | 90 | — | 150 | — |
| Reverse transfer capacitance | C _{re} | V _{CB} = 1 V, I _E = 0, f = 1 MHz (Note) | — | 0.5 | 0.75 | pF |

Note: C_{re} is measured with a three-terminal method using a capacitance bridge.

Caution

This device is sensitive to electrostatic discharge. Ensure that tools and equipment are sufficiently grounded before handling. When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

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